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		APPLICANT Seung-Hyun RHEE, et al.			
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		U.S. PATENT DOCUMENTS			
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		Vincent ARNAL et al. "A Novel SiO ₂ -Air Low K for Copper Dual Damascene Interconnect", Conference Proceedings ULSI XVI (2001) Materials Research Society pp. 71-77.			
		B. SHIEH et al., "Air-Gap Formation During IMD Deposition to Lower Interconnect Capacitance", IEEE Electron Device Letters, Vol. 19, No. 1, January 1998			
		B. P. SHIEH et al., "Integration and Reliability Issues for Low Capacitance Air-Gap Interconnect Structures", 1998 IEEE			
		Vincent Arnal et al., "Optimization of CVD Dielectric Process to Achieve Reliable Ultra Low-k Air Gaps", Microelectronic Engineering 60 (2002) pp. 143-148			
EXAMINER Mahmoud Nakumene		DATE CONSIDERED 8/10/05			

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